

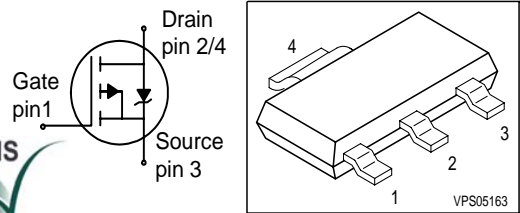
**SIPMOS® Small-Signal-Transistor**  
**Feature**

- P-Channel
- Enhancement mode
- Logic Level
- dv/dt rated
- Pb-free lead plating; RoHS compliant
- Qualified according to AEC Q101
- Halogen-free according to IEC61249-2-21


**Product Summary**

$V_{DS}$	-250	V
$R_{DS(on)}$	12	$\Omega$
$I_D$	-0.26	A

PG-SOT223



Type	Package	Pb-free	Tape and Reel Information	Marking
BSP92P	PG-SOT223	Yes	H6327: 1000 pcs/reel	BSP92P

<b>Packaging</b>
Non dry

**Maximum Ratings, at  $T_j = 25\text{ }^\circ\text{C}$ , unless otherwise specified**

Parameter	Symbol	Value	Unit
Continuous drain current $T_A=25^\circ\text{C}$ $T_A=70^\circ\text{C}$	$I_D$	-0.26 -0.23	A
Pulsed drain current $T_A=25^\circ\text{C}$	$I_{D\text{ puls}}$	-1.04	
Reverse diode dv/dt $I_S=-0.26\text{A}$ , $V_{DS}=-200\text{V}$ , $di/dt=-200\text{A}/\mu\text{s}$ , $T_{j\text{max}}=150^\circ\text{C}$	dv/dt	6	kV/ $\mu\text{s}$
Gate source voltage	$V_{GS}$	$\pm 20$	V
Power dissipation $T_A=25^\circ\text{C}$	$P_{\text{tot}}$	1.8	W
Operating and storage temperature	$T_j, T_{\text{stg}}$	-55... +150	$^\circ\text{C}$
IEC climatic category; DIN IEC 68-1		55/150/56	
ESD Class JESD22-A114-HBM		Class 1a	

**Thermal Characteristics**

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
<b>Characteristics</b>					
Thermal resistance, junction - soldering point (Pin 4)	$R_{thJS}$	-	15	25	K/W
SMD version, device on PCB:	$R_{thJA}$	-	80	115	
@ min. footprint		-	80	115	
@ 6 cm <sup>2</sup> cooling area <sup>1)</sup>		-	48	70	

**Electrical Characteristics, at  $T_j = 25\text{ }^\circ\text{C}$ , unless otherwise specified**

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
<b>Static Characteristics</b>					
Drain-source breakdown voltage $V_{GS}=0, I_D=-250\mu\text{A}$	$V_{(BR)DSS}$	-250	-	-	V
Gate threshold voltage, $V_{GS} = V_{DS}$ $I_D=-130\mu\text{A}$	$V_{GS(th)}$	-1	-1.5	-2	
Zero gate voltage drain current $V_{DS}=-250\text{V}, V_{GS}=0, T_j=25^\circ\text{C}$ $V_{DS}=-250\text{V}, V_{GS}=0, T_j=150^\circ\text{C}$	$I_{DSS}$	-	-0.1	-0.2	$\mu\text{A}$
		-	-10	-100	
Gate-source leakage current $V_{GS}=-20\text{V}, V_{DS}=0$	$I_{GSS}$	-	-10	-100	nA
Drain-source on-state resistance $V_{GS}=-2.8\text{V}, I_D=-0.025\text{A}$	$R_{DS(on)}$	-	10	20	$\Omega$
Drain-source on-state resistance $V_{GS}=-4.5\text{V}, I_D=-0.23\text{A}$	$R_{DS(on)}$	-	8.2	15	
Drain-source on-state resistance $V_{GS}=-10\text{V}, I_D=-0.26\text{A}$	$R_{DS(on)}$	-	7.5	12	

<sup>1)</sup>Device on 40mm\*40mm\*1.5mm epoxy PCB FR4 with 6cm<sup>2</sup> (one layer, 70  $\mu\text{m}$  thick) copper area for drain connection. PCB is vertical without blown air.

**Electrical Characteristics**, at  $T_j = 25\text{ }^\circ\text{C}$ , unless otherwise specified

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

**Dynamic Characteristics**

Transconductance	$g_{fs}$	$ V_{DS}  \geq 2 *  I_D  * R_{DS(on)max}$ , $I_D = -0.23\text{A}$	0.29	0.57	-	S
Input capacitance	$C_{iss}$	$V_{GS} = 0, V_{DS} = -25\text{V}$ , $f = 1\text{MHz}$	-	83	104	pF
Output capacitance	$C_{oss}$		-	13	16	
Reverse transfer capacitance	$C_{rss}$		-	6	8	
Turn-on delay time	$t_{d(on)}$	$V_{DD} = -125\text{V}, V_{GS} = -10\text{V}$ , $I_D = -0.26\text{A}, R_G = 6\Omega$	-	5	8	ns
Rise time	$t_r$		-	6	9	
Turn-off delay time	$t_{d(off)}$		-	67	101	
Fall time	$t_f$		-	33	50	

**Gate Charge Characteristics**

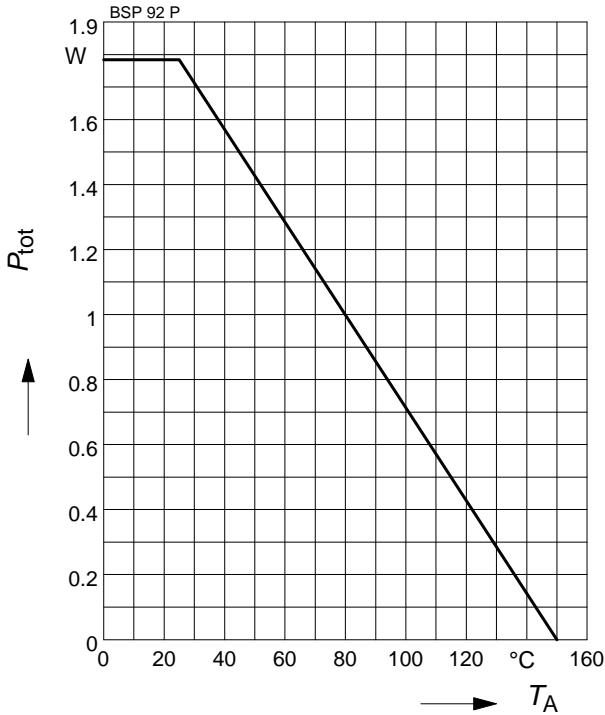
Gate to source charge	$Q_{gs}$	$V_{DD} = -200\text{V}, I_D = -0.26\text{A}$	-	-0.1	-0.13	nC
Gate to drain charge	$Q_{gd}$		-	-1.9	-2.4	
Gate charge total	$Q_g$	$V_{DD} = -200\text{V}, I_D = -0.26\text{A}$ , $V_{GS} = 0 \text{ to } -10\text{V}$	-	-4.3	-5.4	
Gate plateau voltage	$V_{(plateau)}$	$V_{DD} = -200\text{V}, I_D = -0.26\text{A}$	-	-2.9	-3.6	V

**Reverse Diode**

Inverse diode continuous forward current	$I_S$	$T_A = 25^\circ\text{C}$	-	-	-0.26	A
Inv. diode direct current, pulsed	$I_{SM}$		-	-	-1.04	
Inverse diode forward voltage	$V_{SD}$	$V_{GS} = 0, I_F = -0.26\text{A}$	-	-0.83	-1.21	V
Reverse recovery time	$t_{rr}$	$V_R = -125\text{V}, I_F = I_S$ , $di_F/dt = 100\text{A}/\mu\text{s}$	-	51	64	ns
Reverse recovery charge	$Q_{rr}$		-	76	95	

### 1 Power dissipation

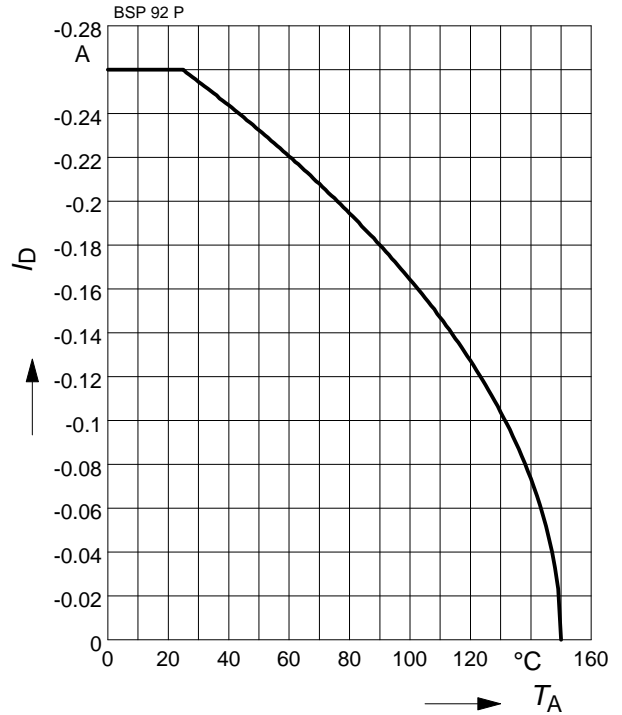
$$P_{tot} = f(T_A)$$



### 2 Drain current

$$I_D = f(T_A)$$

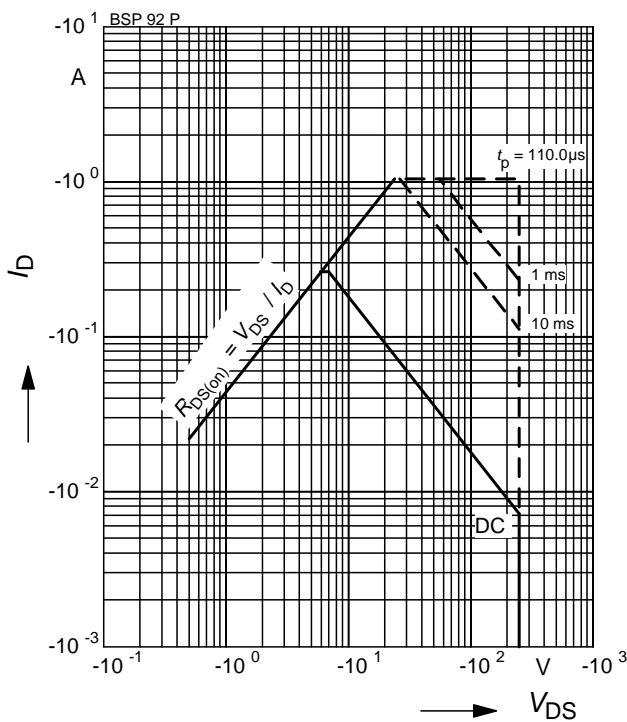
parameter:  $|V_{GS}| \geq 10V$



### 3 Safe operating area

$$I_D = f(V_{DS})$$

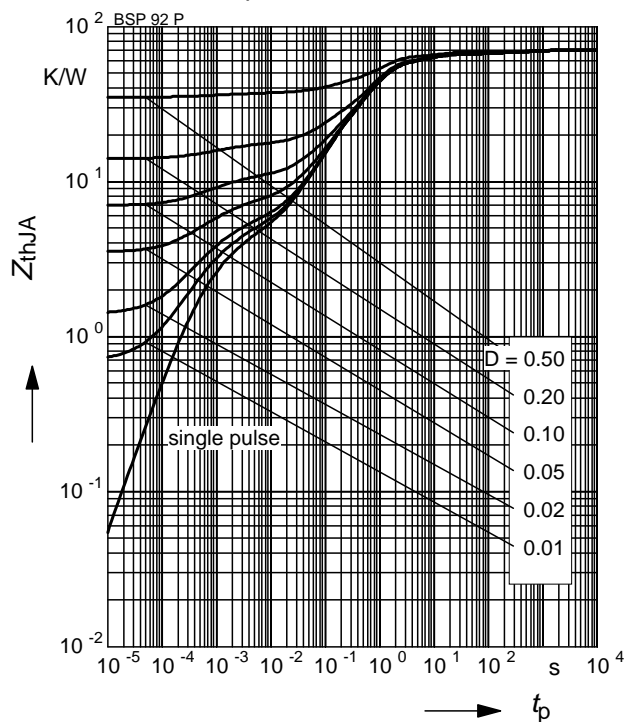
parameter:  $D = 0, T_A = 25^\circ C$



### 4 Transient thermal impedance

$$Z_{thJA} = f(t_p)$$

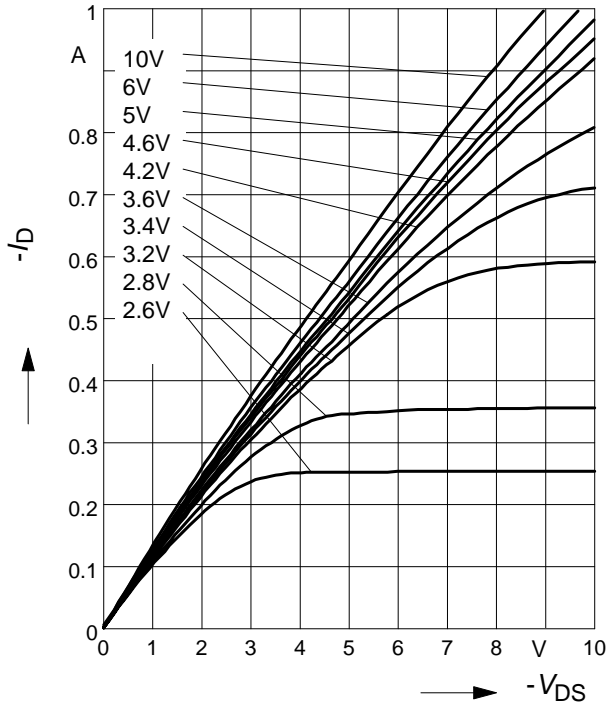
parameter:  $D = t_p/T$



**5 Typ. output characteristic**

$I_D = f(V_{DS})$

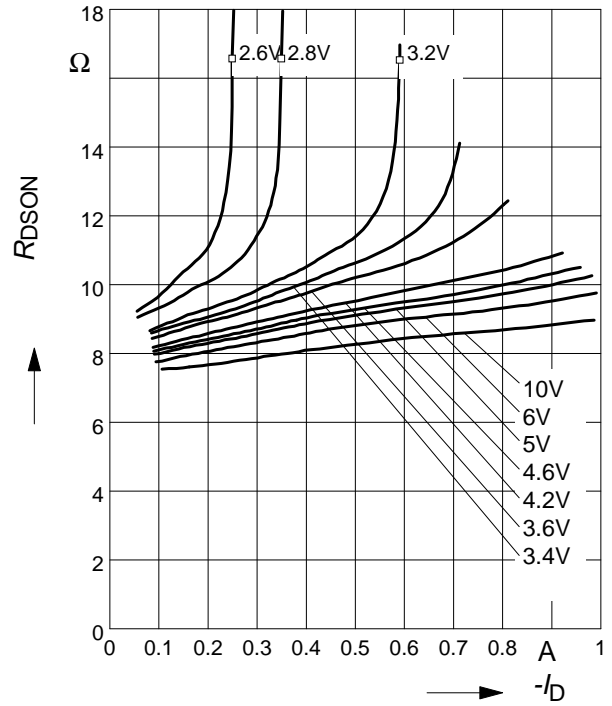
parameter:  $T_j = 25^\circ\text{C}$ ,  $-V_{GS}$



**6 Typ. drain-source on resistance**

$R_{DS(on)} = f(I_D)$

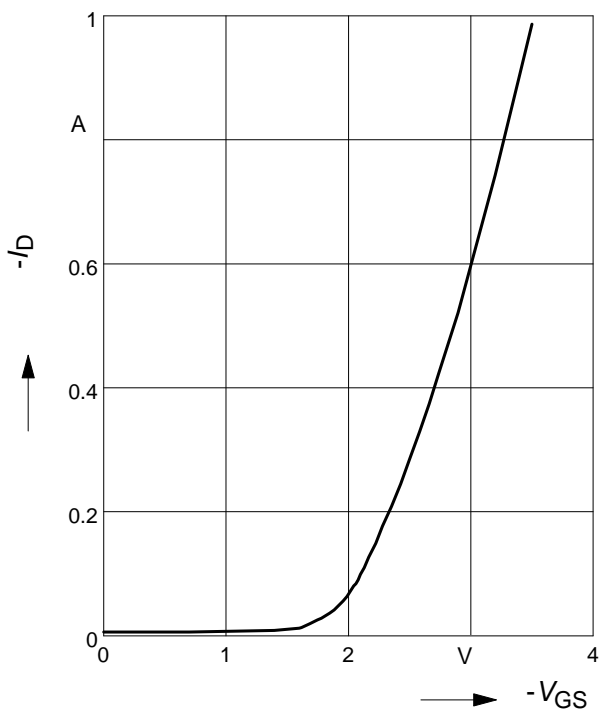
parameter:  $V_{GS}$ ;  $T_j = 25^\circ\text{C}$ ,  $-V_{GS}$



**7 Typ. transfer characteristics**

$I_D = f(V_{GS})$ ;  $|V_{DS}| \geq 2 \times |I_D| \times R_{DS(on)max}$

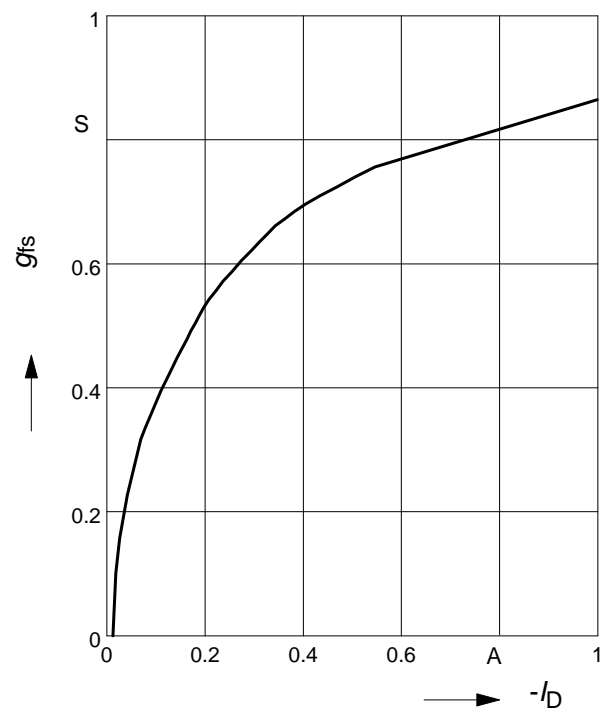
parameter:  $T_j = 25^\circ\text{C}$



**8 Typ. forward transconductance**

$g_{fs} = f(I_D)$

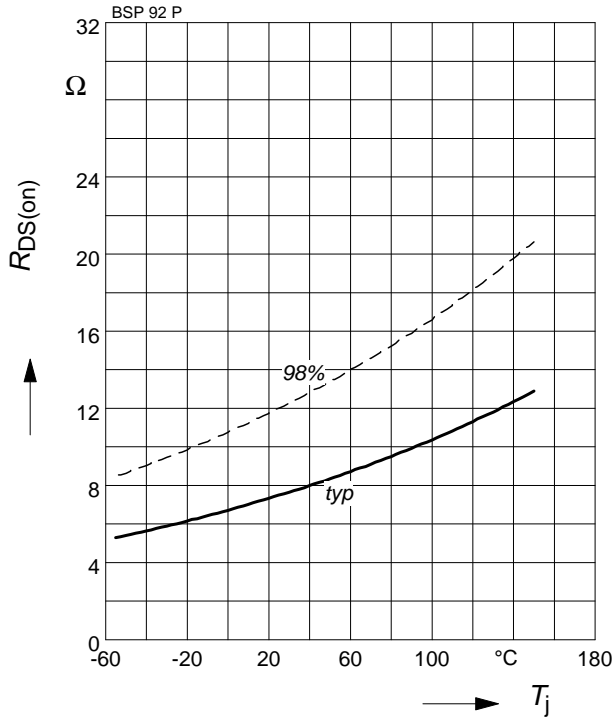
parameter:  $T_j = 25^\circ\text{C}$



**9 Drain-source on-state resistance**

$$R_{DS(on)} = f(T_j)$$

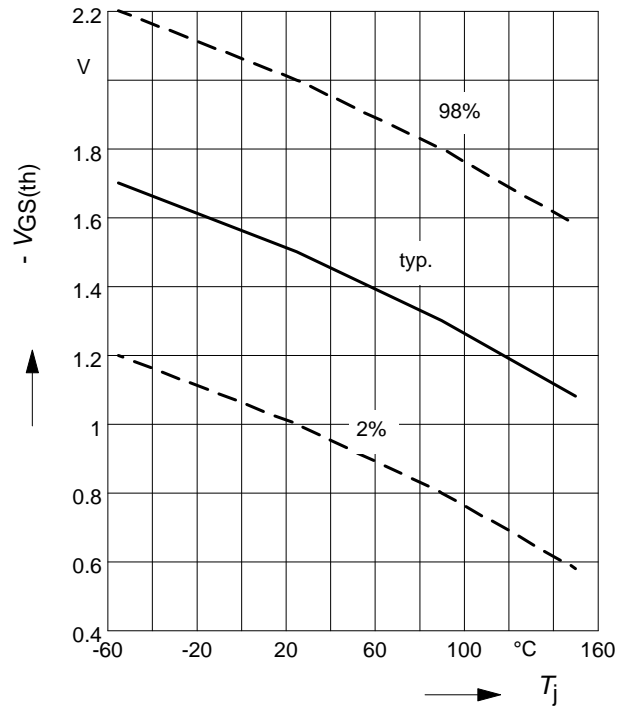
parameter:  $I_D = -0.26 \text{ A}$ ,  $V_{GS} = -10 \text{ V}$



**10 Gate threshold voltage**

$$V_{GS(th)} = f(T_j)$$

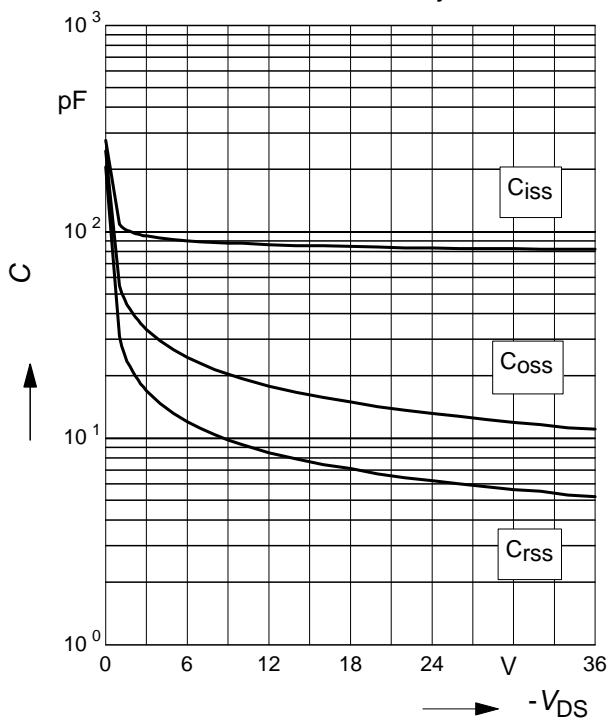
parameter:  $V_{GS} = V_{DS}$ ;  $I_D = -130 \mu\text{A}$



**11 Typ. capacitances**

$$C = f(V_{DS})$$

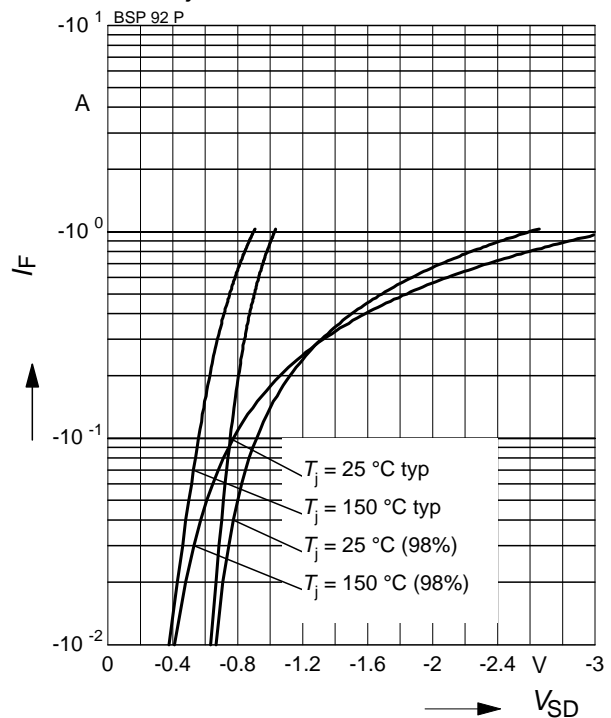
parameter:  $V_{GS}=0$ ,  $f=1 \text{ MHz}$ ,  $T_j = 25 \text{ }^\circ\text{C}$



**12 Forward character. of reverse diode**

$$I_F = f(V_{SD})$$

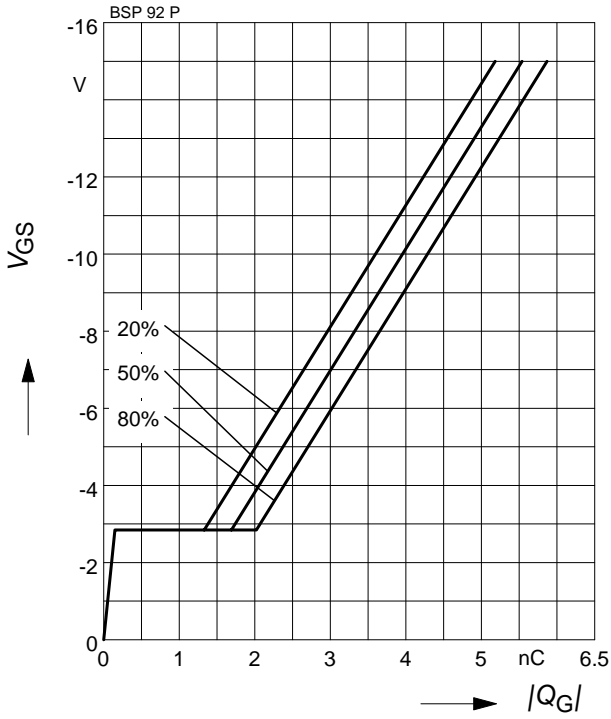
parameter:  $T_j$



**13 Typ. gate charge**

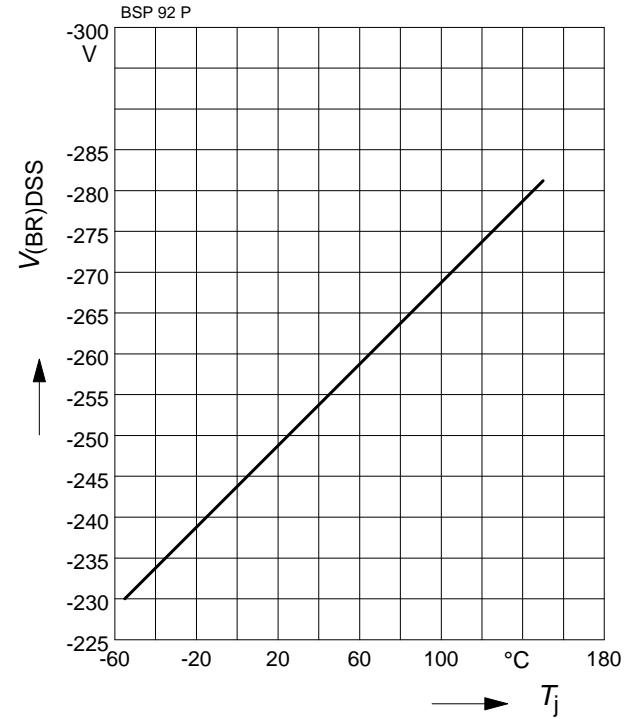
$$V_{GS} = f(Q_{Gate})$$

parameter:  $I_D = -0.26$  A pulsed



**14 Drain-source breakdown voltage**

$$V_{(BR)DSS} = f(T_j)$$



**Published by**  
**Infineon Technologies AG**  
**81726 Munich, Germany**  
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